



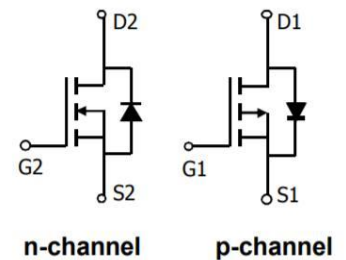
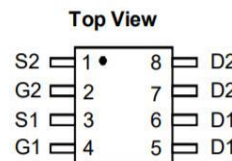
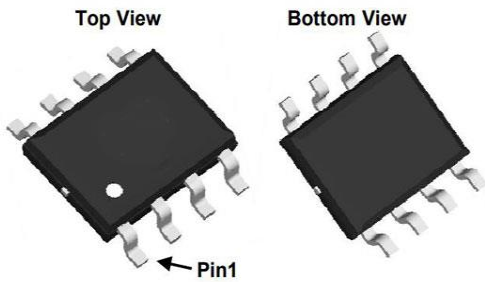
N+P Complementary Power MOSFET

General Description

0  
 Very low on-resistance  $R_{DS(on)}$  @  $V_{GS}=4.5\text{ V}$   
 Pb-free lead plating; RoHS compliant

N channel P channel

$V_{DS}$	30	-30	V
$R_{DS(on),TYP@V_{GS}=10V}$	29.4	38.5	$m\Omega$
$R_{DS(on),TYP@V_{GS}=4.5}$	46.2	38.5	$m\Omega$
$I_D$	6	38.5	A



Part ID	Package Type	Marking	Tape and reel information
SM4620PRL	SOP8	4620	3000



100% UIS Tested

Parameter	Symbol	Max N-channel	Max P-channel	Units	
Drain-Source Voltage	$V_{DS}$	30	-30	V	
Gate-Source Voltage	$V_{GS}$	20	20	$\pm V$	
Continuous Drain Current <sup>A</sup>	$I_D$	$T_A=25^\circ C$	6	-5.3	A
		$T_A=70^\circ C$	5	-4.5	
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	9.6	-8.5		
Avalanche Current <sup>G</sup>	$I_{AR}$	1.92	-1.7		
Repetitive avalanche energy $L=0.1mH$ <sup>G</sup>	$E_{AR}$	4.416	-3.9	mJ	
Power Dissipation <sup>A</sup>	$P_D$	$T_A=25^\circ C$	2	2	W
		$T_A=70^\circ C$	1.3	1.44	
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	-55 to 150	$^\circ C$	

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	105	157	$^\circ C/W$
Maximum Junction-to-Ambient <sup>A</sup>		Steady State	210	252
Maximum Junction-to-Lead <sup>c</sup>	$R_{\theta JL}$	63	100	$^\circ C/W$



N+P Complementary Power MOSFET

**STATIC PARAMETERS**

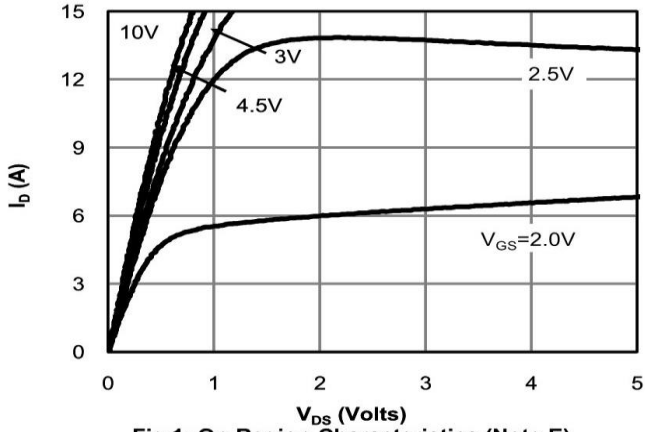
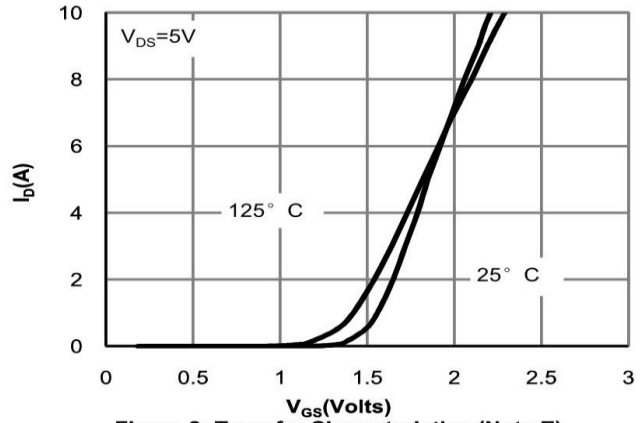
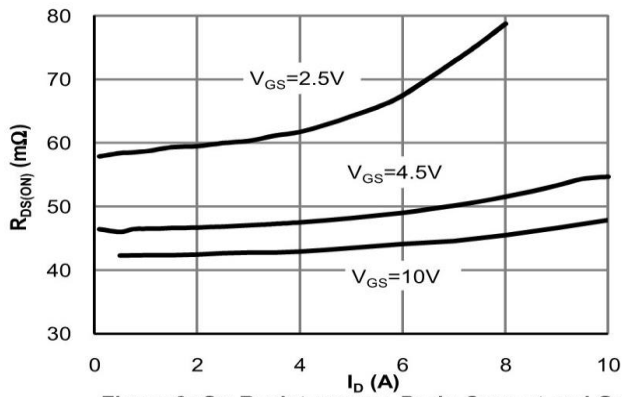
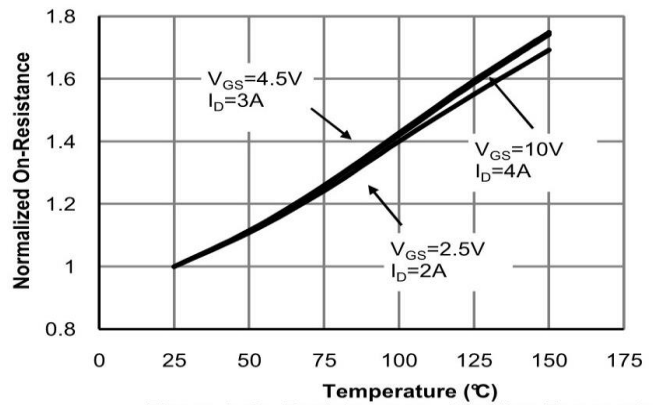
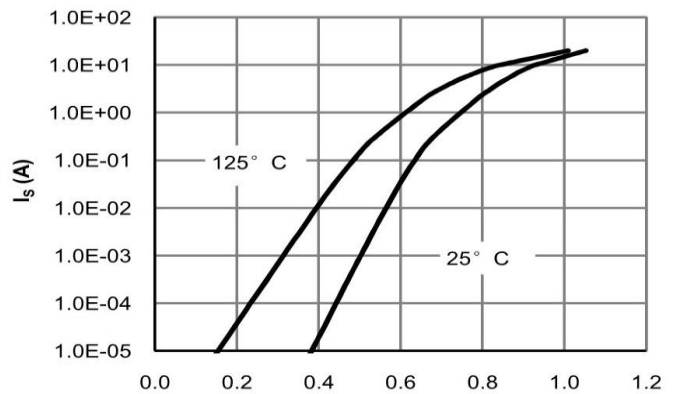
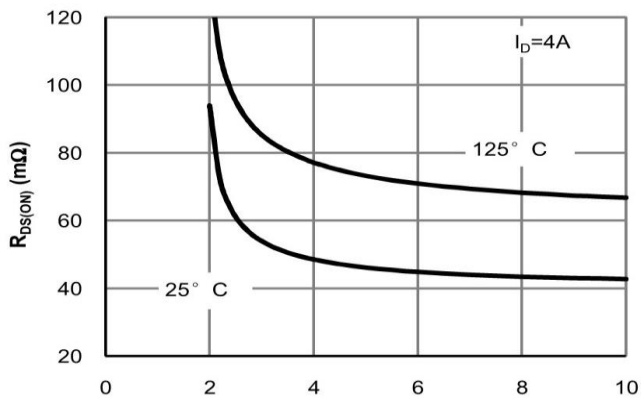
Symbol	Parameter	Conditions	Min	Typ	Max	Units
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> = -250uA, V <sub>GS</sub> = 0V	30			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			1	uA
					5	
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±20V			±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> I <sub>D</sub> = 250µA	1.2	1.8	2.4	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	#REF!		29.4	42.0	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =6A		46.2	60.1	
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =6A		83		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =1A, V <sub>GS</sub> =18V		0.72	1	V
I <sub>S</sub>	Maximum Body-Diode Continuous Current				6	A

**DYNAMIC PARAMETERS**

Symbol	Parameter	Conditions	Min	Typ	Max	Units
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =15V, f=1MHz		255	311	pF
C <sub>oss</sub>	Output Capacitance			45	55	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			35	41	pF
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz			0.65	Ω

**SWITCHING PARAMETERS**

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Q <sub>g</sub> (10V)	Total Gate Charge	V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, I <sub>D</sub> =6A		2.55		nC
Q <sub>g</sub> 4.5V)	Total Gate Charge			1.275		
Q <sub>gs</sub>	Gate Source Charge			0.91		
Q <sub>gd</sub>	Gate Drain Charge			1.3		
t <sub>D(on)</sub>	Turn-On DelayTime	V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, R <sub>L</sub> =0.75Ω, R <sub>GEN</sub> =3Ω		4.25		ns
t <sub>r</sub>	Turn-On Rise Time			3.4		
t <sub>D(off)</sub>	Turn-Off DelayTime			11.9		
t <sub>f</sub>	Turn-Off Fall Time			3.825		
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =-8A, dI/dt=500A/µs		8.5		ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =18A, dI/dt=500A/µs		2.2		nC

**N+P Complementary Power MOSFET**
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**

**Fig 1: On-Region Characteristics (Note E)**

**Figure 2: Transfer Characteristics (Note E)**

**Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)**

**Figure 4: On-Resistance vs. Junction Temperature (Note E)**




N+P Complementary Power MOSFET

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

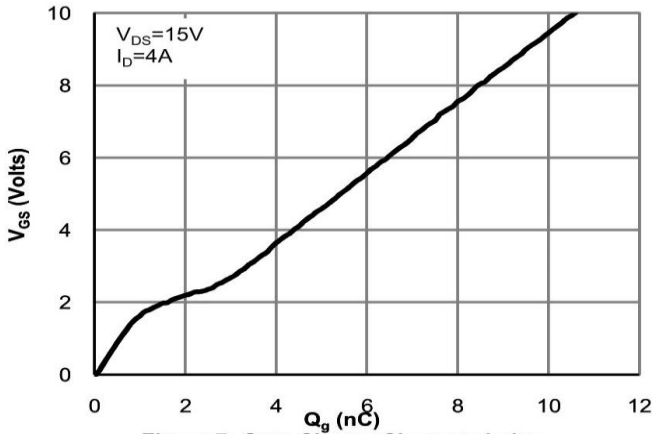


Figure 7: Gate-Charge Characteristics

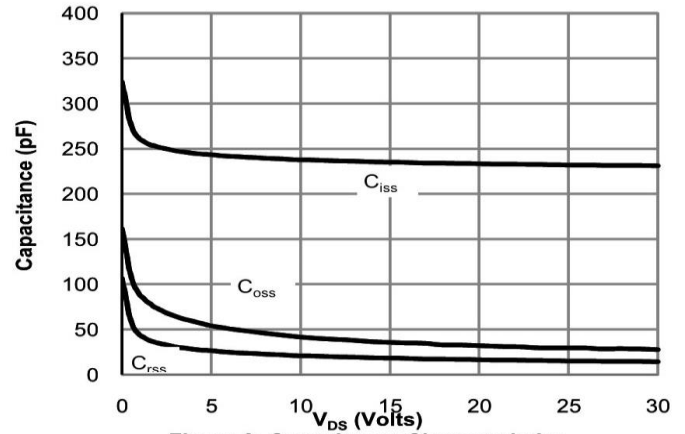


Figure 8: Capacitance Characteristics

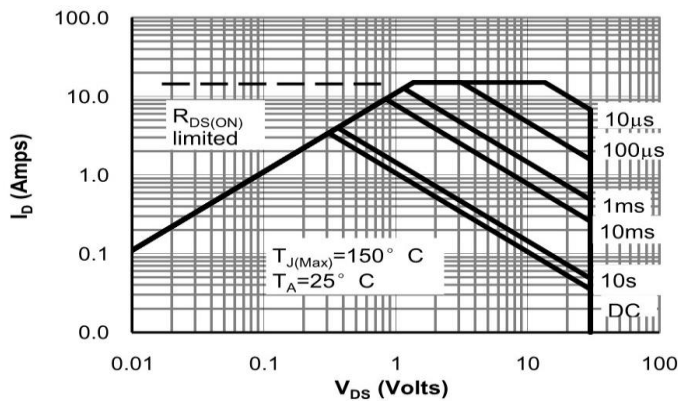


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

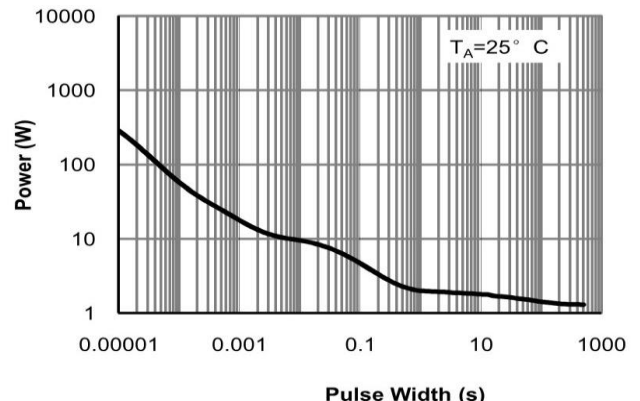


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

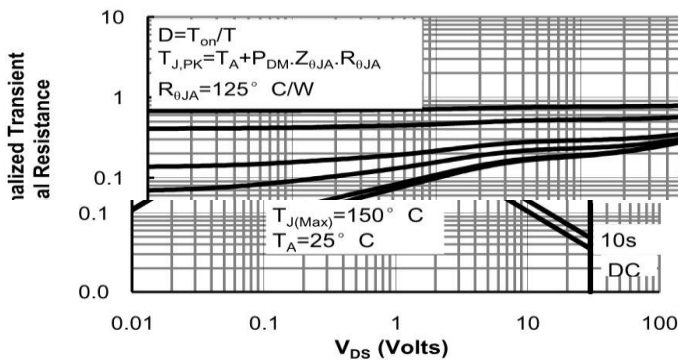


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

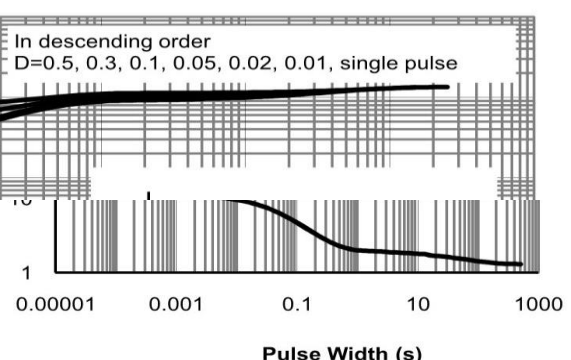
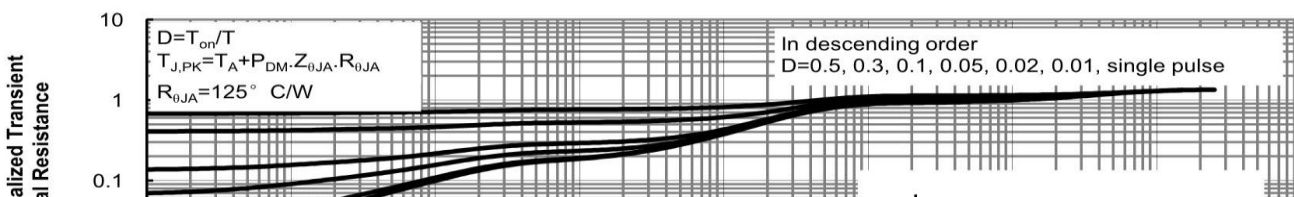


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)



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